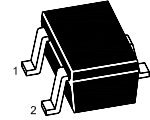


PNP Silicon Epitaxial Planar Transistor

The transistor is subdivided into three groups Q, R and S according to its DC current gain.



1.Base 2.Emitter 3.Collector
SOT-323 Plastic Package

Absolute Maximum Ratings ($T_a = 25\text{ }^\circ\text{C}$)

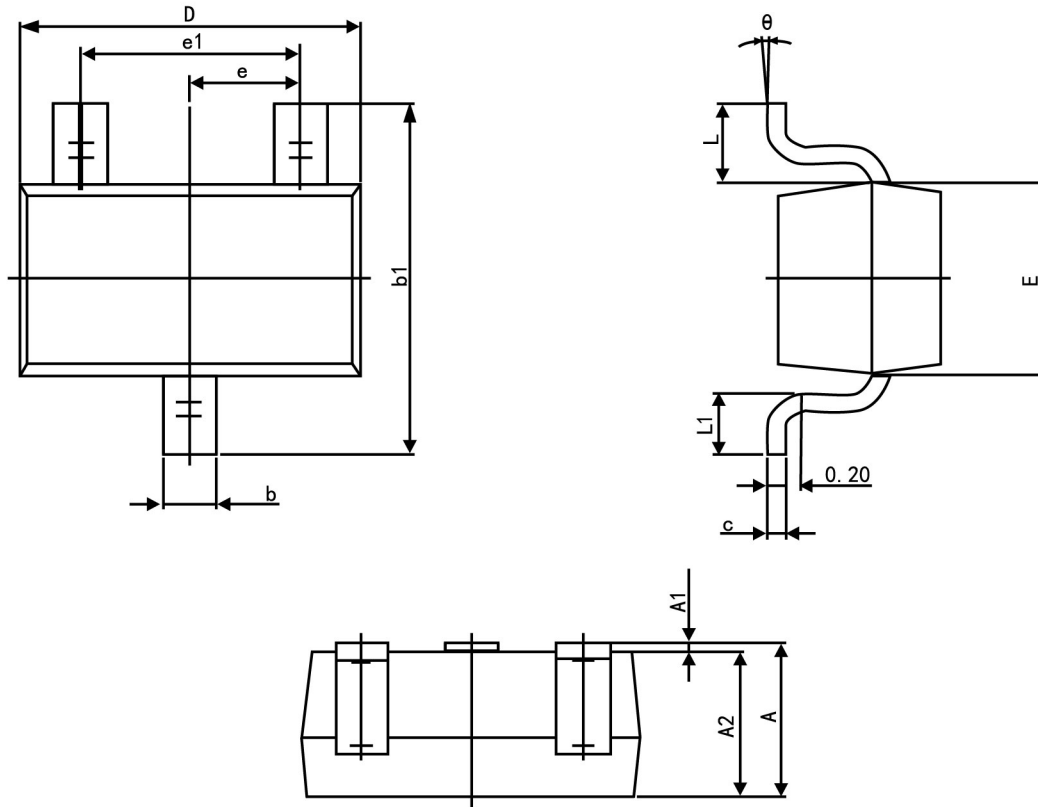
Parameter	Symbol	Value	Unit
Collector Base Voltage	$-V_{CBO}$	60	V
Collector Emitter Voltage	$-V_{CEO}$	50	V
Emitter Base Voltage	$-V_{EBO}$	6	V
Collector Current	$-I_C$	150	mA
Power Dissipation	P_{tot}	200	mW
Junction Temperature	T_j	150	$^\circ\text{C}$
Storage Temperature Range	T_{stg}	- 55 to + 150	$^\circ\text{C}$

Characteristics at $T_a = 25\text{ }^\circ\text{C}$

Parameter	Symbol	Min.	Typ.	Max.	Unit
DC Current Gain at $-V_{CE} = 6\text{ V}$, $-I_C = 1\text{ mA}$ Current Gain Group	Q h_{FE}	120	-	270	-
	R h_{FE}	180	-	390	-
	S h_{FE}	270	-	560	-
Collector Base Cutoff Current at $-V_{CB} = 60\text{ V}$	$-I_{CBO}$	-	-	0.1	μA
Emitter Base Cutoff Current at $-V_{EB} = 6\text{ V}$	$-I_{EBO}$	-	-	0.1	μA
Collector Base Breakdown Voltage at $-I_C = 50\text{ }\mu\text{A}$	$-V_{(BR)CBO}$	60	-	-	V
Collector Emitter Breakdown Voltage at $-I_C = 1\text{ mA}$	$-V_{(BR)CEO}$	50	-	-	V
Emitter Base Breakdown Voltage at $-I_E = 50\text{ }\mu\text{A}$	$-V_{(BR)EBO}$	6	-	-	V
Collector Emitter Saturation Voltage at $-I_C = 50\text{ mA}$, $-I_B = 5\text{ mA}$	$-V_{CE(sat)}$	-	-	0.5	V
Transition Frequency at $-V_{CE} = 12\text{ V}$, $-I_E = 2\text{ mA}$, $f = 30\text{ MHz}$	f_T	-	140	-	MHz
Collector Output Capacitance at $-V_{CB} = 12\text{ V}$, $f = 1\text{ MHz}$	C_{ob}	-	-	5	pF



SOT-323 Package Outline Dimensions



Symbol	Dimension in Millimeters	
	Min	Max
A	0.900	1.100
A1	0.000	0.100
A2	0.900	1.000
b	0.200	0.400
c	0.080	0.150
D	2.000	2.200
E	1.150	1.350
E1	2.150	2.450
e	0.650 TYP.	
e1	1.200	1.400
L	0.525 REF.	
L1	0.260	0.460
theta	0°	8°